gXOB0013 B
W-band X8 MMIC multiplier
82 – 91 (80 – 94) GHz

FEATURES

- W-band, 82 – 91 GHz
- Output power, 11 dBm typ.
- Harmonic isolation, 20 dBc typ.

TYPICAL APPLICATIONS

- W-band point-to-point radio
- Active imaging and sensors
- Test instrumentation

DESCRIPTION

The gXOB0013 GaAs pHEMT MMIC is an efficient X8 W-band multiplier ideal for point to point radio and radar applications. The chip has an integrated output buffer. At the recommended drive level of 10 dBm the output power is typically 11 dBm with better than 20 dBc harmonic isolation and 400 mW power dissipation.

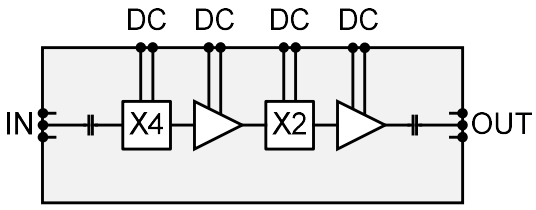

Figure 1. Circuit functional diagram.

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ELECTRICAL PERFORMANCE

Table 1. Electrical performance T_A=25C

Parameter	Min	Typ	Max	Unit
Output frequency	82		91	GHz
Input frequency	10.2		11.4	GHz
Multiplication factor		8		
Output power	9	11		dBm
Output power flatness		1		dBpp
Recommended input drive power		10		dBm
Harmonic isolation (relative to X8 output)		20		dBc
Output return loss	10			dB
Input return loss	5			dB
Power dissipation (signal off)		220		mW
Power dissipation (signal on)	350	400	450	mW

MEASURED PERFORMANCE

Measurements have been performed on-wafer at room temperature with typical bias settings and an input drive power if not specified otherwise.

Table 2. Test conditions

Parameter	Setting
Input drive power	10 dBm
Temperature	25°C

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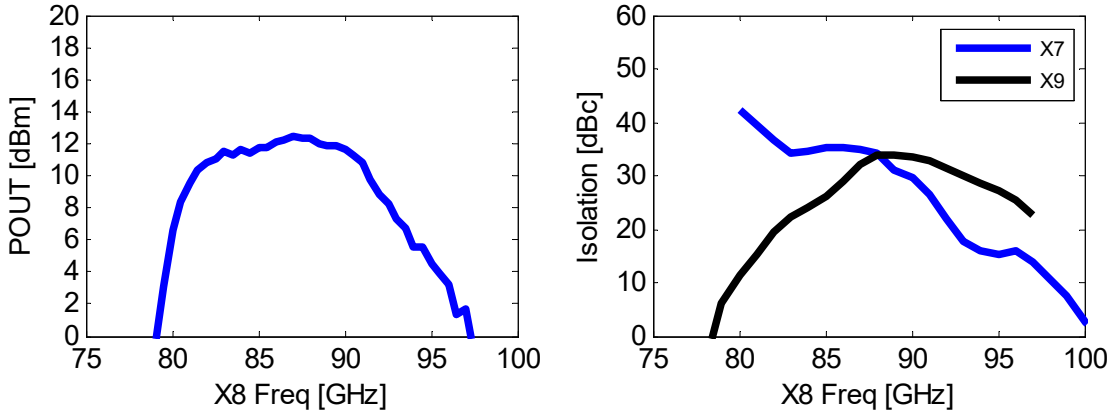

Figure 2. Output power vs X8 output frequency (left). Harmonic isolation vs X8 output frequency (right).

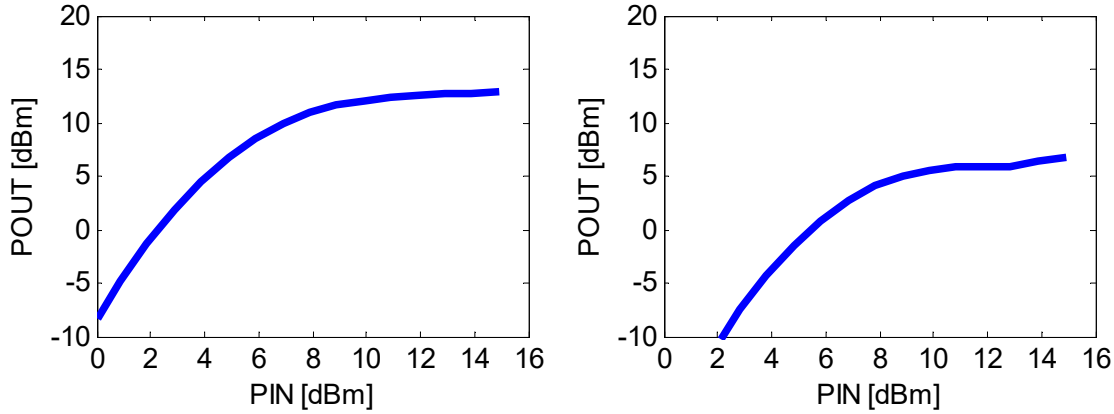

Figure 3. Output power vs input power at 86 GHz (left). Output power vs input power at 94 GHz (right).

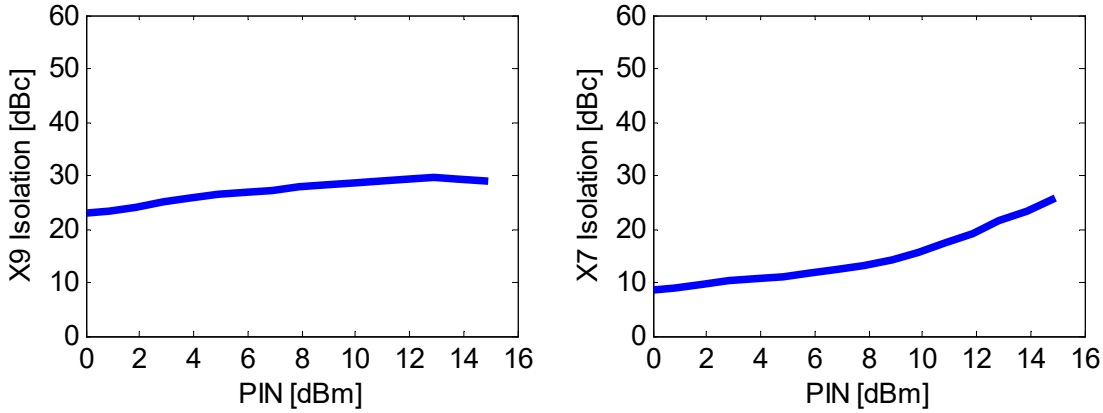

Figure 4. X9 isolation vs input power at 86 GHz (left). X7 isolation vs input power at 94 GHz (right).

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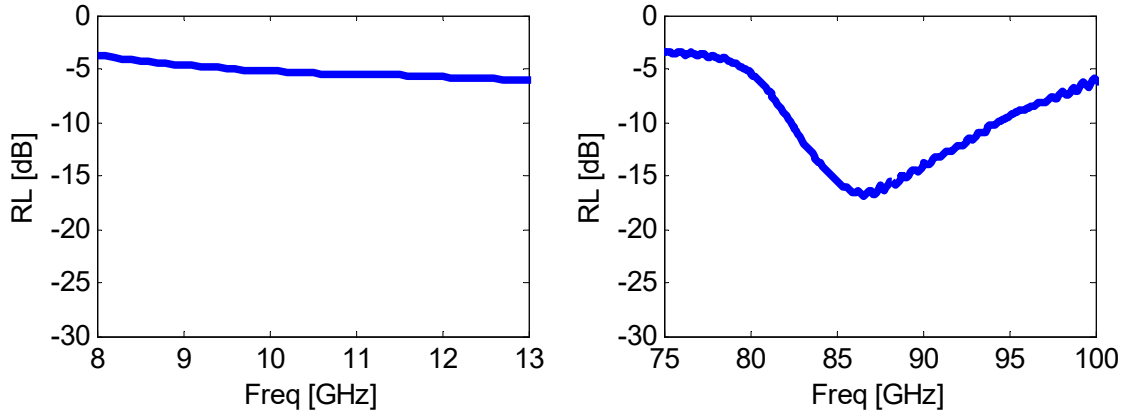

Figure 5. Input return loss (left). Output return loss (right).

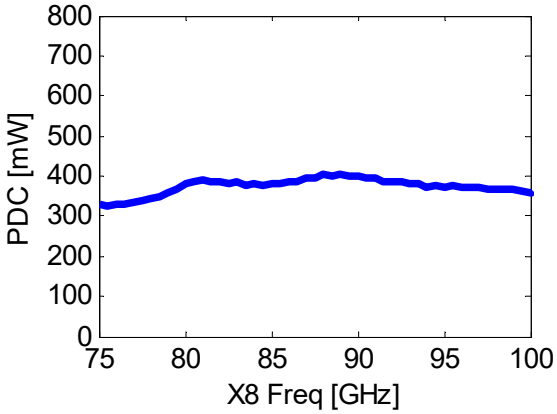

Figure 6. Power dissipation vs X8 output frequency.

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RECOMMENDED OPERATING CONDITIONS

Apply the gate (VG_…) supplies first followed by the drain (VD_…) supplies. Gate voltages are adjusted within the typical min/max range to obtain the specified drain currents. The drain currents are stated with all input signals off.

Table 3. Electrical settings, P1 pads

Connector P1	Pad No.	Bias settings (V / mA)			Function
		Min	Typ	Max	
VD_BA_2	1	2.9	3.0 / 50	3.1	Input
VG_BA_2	2	-0.5	-0.3	-0.1	Input
VD_X2	3	2.9	3.0 / 3	3.1	Input
VG_X2	4	-1.05	-0.85	-0.65	Input
GND	5				Ground
VD_BA_1	6	2.9	3.0 / 20	3.1	Input
VG_BA_1	7	-0.5	-0.3	-0.1	Input
VD_X4	8	2.9	3.0 / 5	3.1	Input
VG_X4	9	-1.05	-0.85	-0.65	Input

Table 4. Electrical settings, P2 pads

Connector P2	Pad No.	Settings	Function
GND	1		Ground
RF_OUT	2	50 Ohm, open-circuit at DC	Output
GND	3		Ground

Table 5. Electrical settings, P3 pads

Connector P3	Pad No.	Settings	Function
GND	1		Ground
RF_IN	2	50 Ohm, open-circuit at DC	Input
GND	3		Ground

ABSOLUTE MAXIMUM RATINGS

Table 6. Absolute Maximum Ratings

Gate supply voltage	-2 to + 0.7 V
Drain supply voltage	4.5 V
Gate-drain breakdown	8 V
ID_BA_2	120 mA
ID_X2	40 mA
ID_BA_1	30 mA
ID_X4	80 mA
Input level	+ 15 dBm
Operating temperature	-40 to + 85 C
Storage temperature	-65 to +150 C

OUTLINE DRAWING

Dimensions are in µm. Substrate thickness is 50 µm (GaAs). Drawing is also available in dxf-file format on the web.

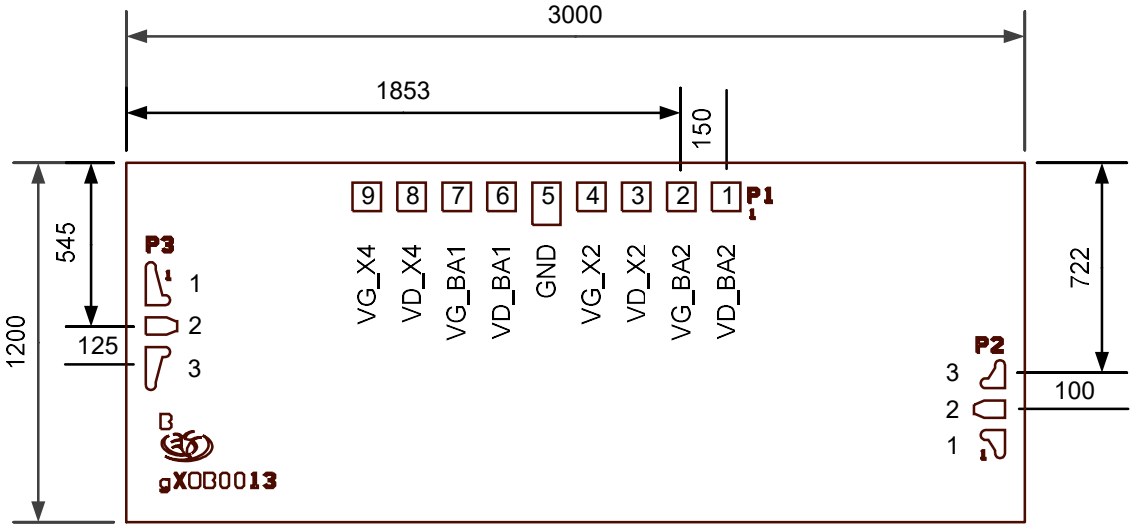

Figure 7. Outline drawing, dimensions are in um.